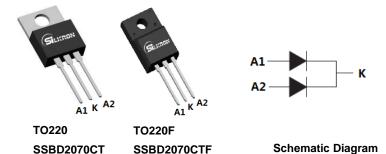


Main Product Characteristics:

IF	2×10A
VRRM	70V
T _j (max)	150 ℃
Vf(max)	0.65V



Features and Benefits:

- High Junction Temperature
- High ESD Protection
- High Forward & Reverse Surge capability



Description:

Schottky Barrier Rectifier designed for high frequency switch model power supplies such as adaptors and DC/DC convertors; this product special design for high forward and reverse surge capability

Absolute Rating:

Symbol	Characterizes	Value	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage	70	V	
V _{R(RMS)}	RMS Reverse Voltage	49	V	
	Average Femiliard Comment	Per diode	10	Α
I _{F(AV)}	Average Forward Current	Per device	20	Α
I _{FSM}	Non Repetitive Surge Forward Curre	180	Α	
I _{RRM}	Peak Repetitive Reverse Surge Curr	2	Α	
TJ	Maximum operation Junction Temper	-55~150	$^{\circ}$	
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}$ C	

Thermal Resistance

Symbol	Characterizes	Value	Unit	
$R_{ heta JC}$	Maximum Thermal Resistance Junction To	2	℃W	
$R_{ heta JC}$	Case(per leg)	TO220F	4	℃W

Electrical Characterizes @T_A=25°C unless otherwise specified

Symbol	Characterizes	Min	Тур	Max	Unit	Test Condition
V_R	Reverse Breakdown Voltage	70			٧	I _R =0.5mA
V _F Forward Voltage Drop				0.65	\/	I _F =10A, T _J =25℃
				0.6	V	I _F =10A, T _J =125℃
I _R	Leakage Current			0.2	^	V _R =70V, T _J =25°C
				50	mA	V _R =70V, T _J =125℃

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I-V Curves:

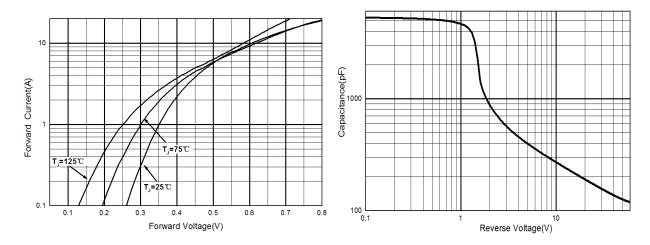


Figure 1: Typical Forward Characteristics Figure 2: Typical Capacitance Characteristics

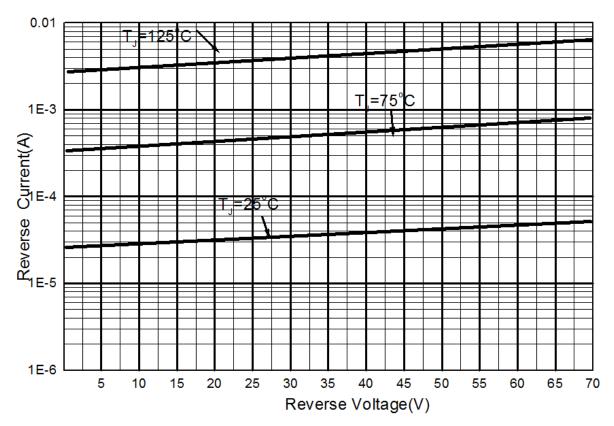


Figure 3: Typical Reverse Characteristics

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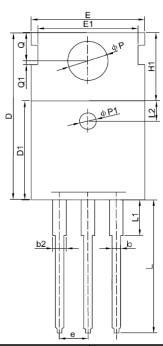
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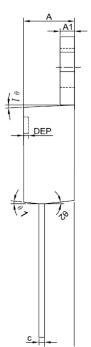
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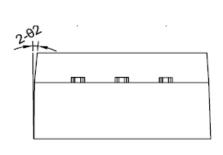


Mechanical Data:

TO220:







Complete	Dime	ension In Millim	eters	Dimension In Inches		
Symbol	Min	Nom	Max	Min	Nom	Max
Α	4.400	4.550	4.700	0.173	0.179	0.185
A1	1.270	1.300	1.330	0.050	0.051	0.052
A2	2.590	2.690	2.790	0.102	0.106	0.110
b	0.770	-	0.900	0.030	-	0.035
b2	1.230	-	1.360	0.048	-	0.054
С	0.480	0.500	0.520	0.019	0.020	0.020
D	15.100	15.400	15.700	-	0.606	-
D1	9.000	9.100	9.200	0.354	0.358	0.362
DEP	0.050	0.285	0.520	0.002	0.011	0.020
Е	10.060	10.160	10.260	0.396	0.400	0.404
E1	-	8.700	-	-	0.343	-
ΦΡ1	1.400	1.500	1.600	0.055	0.059	0.063
е		2.54BSC		0.1BSC		
e1		5.08BSC		0.2BSC		
H1	6.100	6.300	6.500	0.240	0.248	0.256
L	12.750	12.960	13.170	0.502	0.510	0.519
L1	-	-	3.950	-	-	0.156
L2		1.85REF			0.073REF	
ФР	3.570	3.600	3.630	0.141	0.142	0.143
Q	2.730	2.800	2.870	0.107	0.110	0.113
Q1	-	0.200	-	-	0.008	-
θ1	5°	7 ⁰	90	5°	7 ⁰	9º
Θ2	1º	3 ⁰	5°	1º	3º	5º

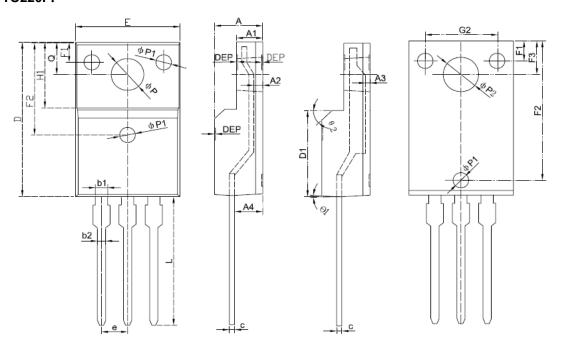
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TO220F:



Compleal	Dimension In Millimeters			Dimension In Inches		
Symbol	Min	Nom	Max	Min	Nom	Max
E	9.960	10.160	10.360	0.392	0.400	0.408
Α	4.500	4.700	4.900	0.177	0.185	0.193
A1	2.340	2.540	2.740	0.092	0.100	0.108
A2	0.950	1.050	1.150	0.037	0.041	0.045
A3	0.420	0.520	0.620	0.017	0.020	0.024
A4	2.650	2.750	2.850	0.104	0.108	0.112
С	-	0.500	-	-	0.020	-
D	15.670	15.870	16.070	0.617	0.625	0.633
Q	3.200	3.300	3.400	0.126	0.130	0.134
H1	6.480	6.680	6.880	0.255	0.263	0.271
е		2.54BSC		0.10BSC		
ФР	-	3.183	-	-	0.125	-
L	12.780	12.980	13.180	0.503	0.511	0.519
D1	8.990	9.190	9.390	0.354	0.362	0.370
ФР1	1.400	1.500	1.600	0.055	0.059	0.063
ФР2	-	3.450	-	-	0.136	-
0 1	4°	5°	6°	4°	5°	6°
Θ2	-	45°	-	-	45°	-
DEP	0.050	0.100	0.150	0.002	0.004	0.006
F1	1.900	2.000	2.100	0.075	0.079	0.083
F2	8.980	9.180	9.380	0.354	0.361	0.369
F3	3.200	3.300	3.400	0.126	0.130	0.134
G2	6.900	7.000	7.100	0.272	0.276	0.280
b1	1.170	1.205	1.240	0.046	0.047	0.049
b2	0.770	0.810	0.850	0.030	0.032	0.033

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Ordering and Marking Information

Device Marking: SSBD2070CT&SSBD2070CTF

Package (Available) TO-220&TO220F **Operating Temperature Range** C: -55 to 150 °C

Devices per Unit

Packag e Type	Units/ Tube	Tubes/Inne r Box	Units/Inne r Box	Inner Boxes/Carton Box	Units/Carto n Box
TO220	50	20	1000	6	6000
TO220F	50	20	1000	6	6000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High	Tj=125℃ to 150℃ @	168 hours	3 lots x 77 devices
Temperature	80% of Max	500 hours	
Reverse	VDSS/VCES/VR	1000 hours	
Bias(HTRB)			



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